



PRODUCT DATA SHEET



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Datasheet



Resources



Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

General Description

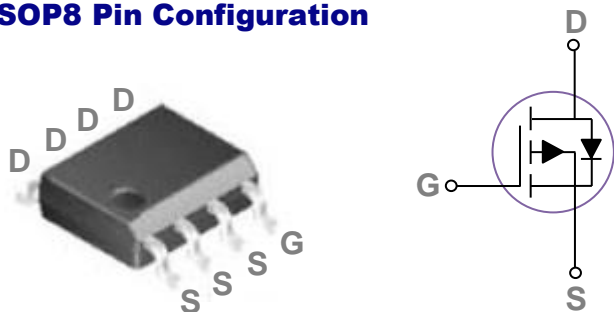
These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
-30V	7.2mΩ	-16A

Features

- -30V, -16A, $R_{DS(ON)} = 7.2m\Omega @ V_{GS} = -10V$
- Fast switching
- Green Device Available
- Suit for -4.5V Gate Drive Applications

SOP8 Pin Configuration



Applications

- MB / VGA / Vcore
- POL Applications
- Load Switch
- LED Application

Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_A=25^\circ\text{C}$)	-16	A
	Drain Current – Continuous ($T_A=70^\circ\text{C}$)	-12.8	A
I_{DM}	Drain Current – Pulsed ¹	-64	A
EAS	Single Pulse Avalanche Energy ²	125	mJ
IAS	Single Pulse Avalanche Current ²	-50	A
P_D	Power Dissipation ($T_A=25^\circ\text{C}$)	3.1	W
	Power Dissipation – Derate above 25°C	0.025	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	---	40	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30	---	---	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-30V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-24V, V _{GS} =0V, T _J =125°C	---	---	-10	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-6A	---	6	7.2	mΩ
		V _{GS} =-4.5V, I _D =-4A	---	8.6	12	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.0	-1.6	-2.5	V
g _{fs}	Forward Transconductance	V _{DS} =-10V, I _D =-1A	---	7	---	S

Dynamic and switching Characteristics

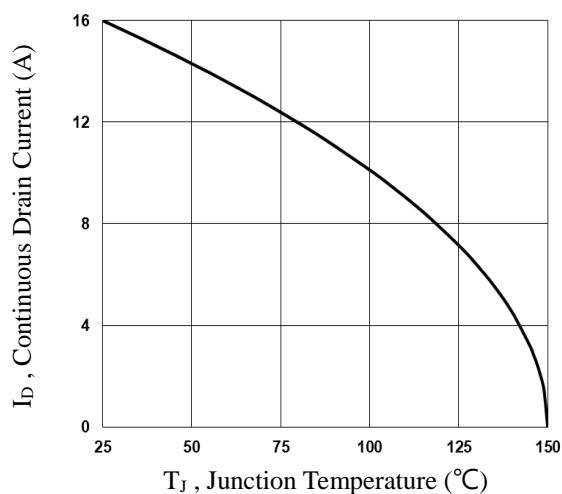
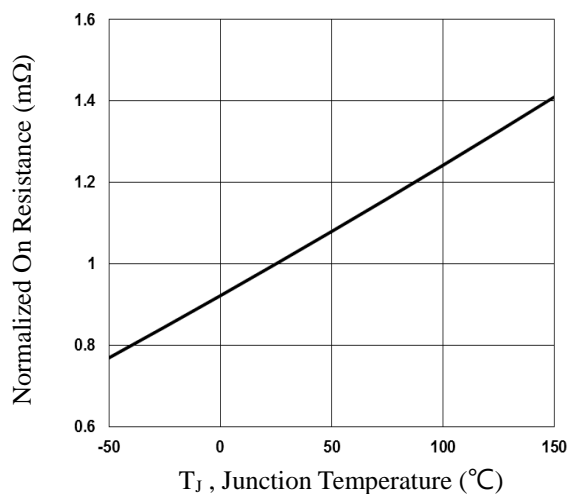
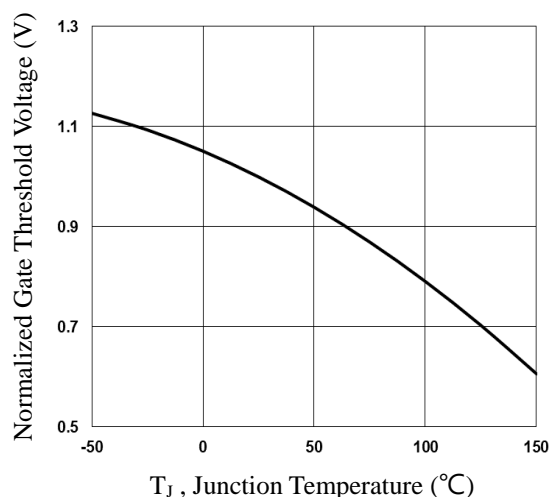
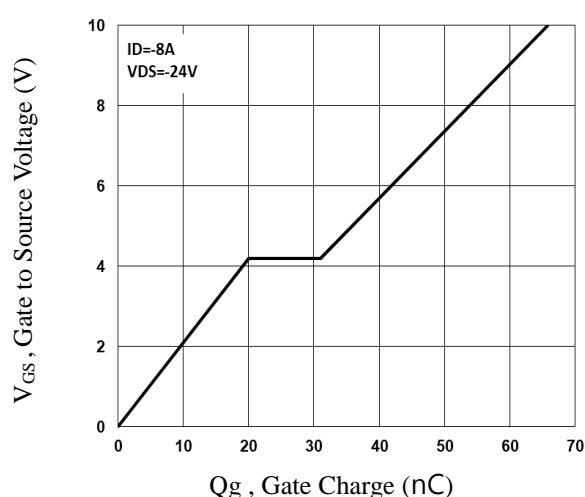
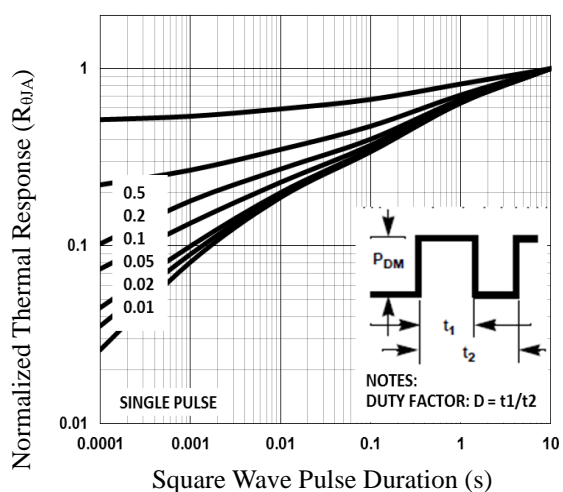
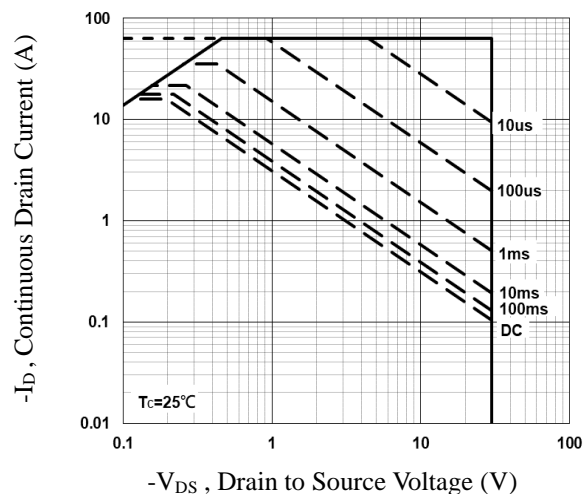
Q _g	Total Gate Charge ^{3, 4}	V _{DS} =-24V, V _{GS} =-10V, I _D =-8A	---	65.8	100	nC
Q _{gs}	Gate-Source Charge ^{3, 4}		---	20	30	
Q _{gd}	Gate-Drain Charge ^{3, 4}		---	11	16	
T _{d(on)}	Turn-On Delay Time ^{3, 4}	V _{DD} =-15V, V _{GS} =-10V, R _G =3.3Ω I _D =-1A	---	35	---	ns
T _r	Rise Time ^{3, 4}		---	14	---	
T _{d(off)}	Turn-Off Delay Time ^{3, 4}		---	235	---	
T _f	Fall Time ^{3, 4}		---	85	---	
C _{iss}	Input Capacitance	V _{DS} =-24V, V _{GS} =0V, F=1MHz	---	3875	5810	pF
C _{oss}	Output Capacitance		---	505	560	
C _{rss}	Reverse Transfer Capacitance		---	380	570	
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	---	6.9	---	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	-13	A
I _{SM}	Pulsed Source Current ²		---	---	-26	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1	V
T _{rr}	Reverse Recovery Time	V _R =30V, I _S =10A, di/dt=100A/μs, T _J =25°C	---	235	---	ns
Q _{rr}	Reverse Recovery Charge		---	337	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=50A., R_G=25Ω, Starting T_J=25°C.
3. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
4. Essentially independent of operating temperature.


Fig.1 Continuous Drain Current vs. T_J

Fig.2 Normalized $R_{DS(on)}$ vs. T_J

Fig.3 Normalized V_{th} vs. T_J

Fig.4 Gate Charge Waveform

Fig.5 Normalized Transient Impedance

Fig.6 Maximum Safe Operation Area

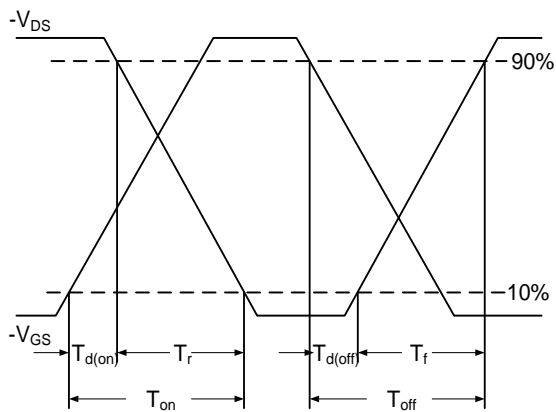


Fig.7 Switching Time Waveform

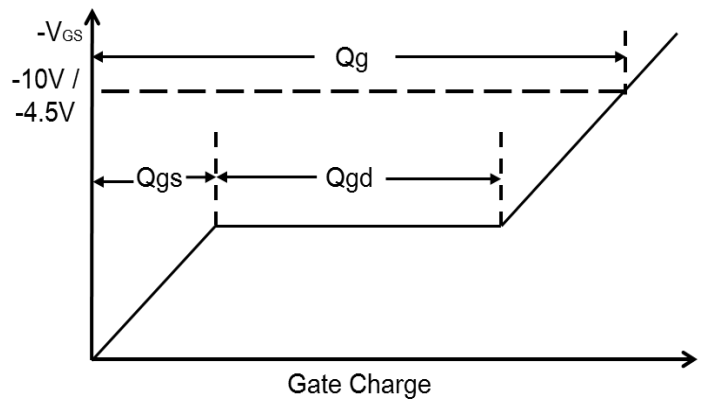
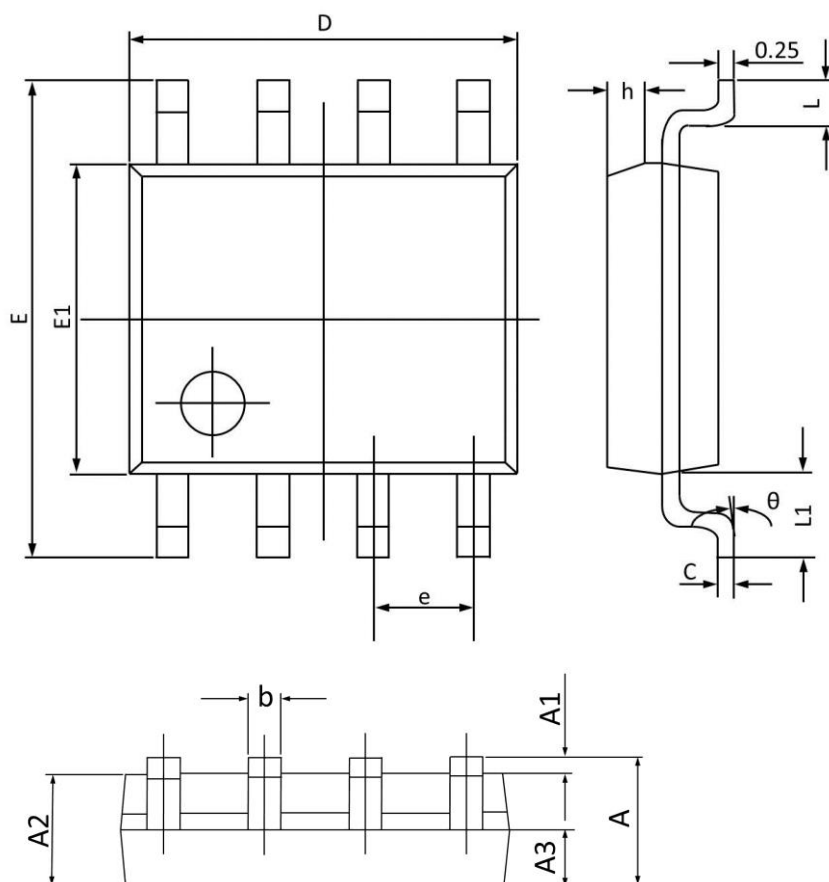


Fig.8 Gate Charge Waveform

SOP8 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.068
A1	0.100	0.250	0.004	0.009
A2	1.300	1.500	0.052	0.059
A3	0.600	0.700	0.024	0.027
b	0.390	0.480	0.016	0.018
c	0.210	0.260	0.009	0.010
D	4.700	5.100	0.186	0.200
E	5.800	6.200	0.229	0.244
E1	3.700	4.100	0.146	0.161
e	1.270(BSC)		0.050(BSC)	
h	0.250	0.500	0.010	0.019
L	0.500	0.800	0.019	0.031
L1	1.050(BSC)		0.041(BSC)	
θ	0°	8°	0°	8°

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